TOSHIBA Transistor Silicon NPN Triple Diffused Type

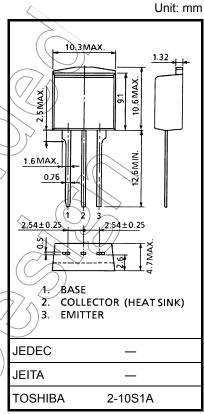
2SC5361

High-Voltage Switching Applications Switching Regulator Applications DC-DC Converter Applications

- Excellent switching times: t_f = 0.5 μs (max) (IC = 1.2 A)
- High breakdown voltage: $V_{CEO} = 800 \text{ V}$
- High DC current gain: $h_{FE} = 15$ (min) ($I_{C} = 0.15$ A)

Absolute Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	900	y	
Collector-emitter voltage		V _{CEO}	800	> v	
Emitter-base voltage		V _{EBO}	Z	V	
Collector current	DC	IC	3	A	
	Pulse	I _{CP}	5		
Base current		I _B	1	A	
Collector power dissipation	Ta = 25°C	PC	1.5	. w	
	Tc = 25°C	PC \	40		
Junction temperature		(T_j)	150	//°C	
Storage temperature range		T _{stg}	-55 to 150	ŝ	



Weight: 1.5 g (typ.)

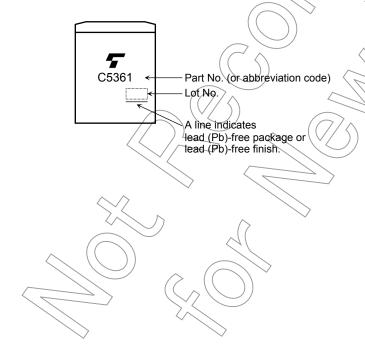
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

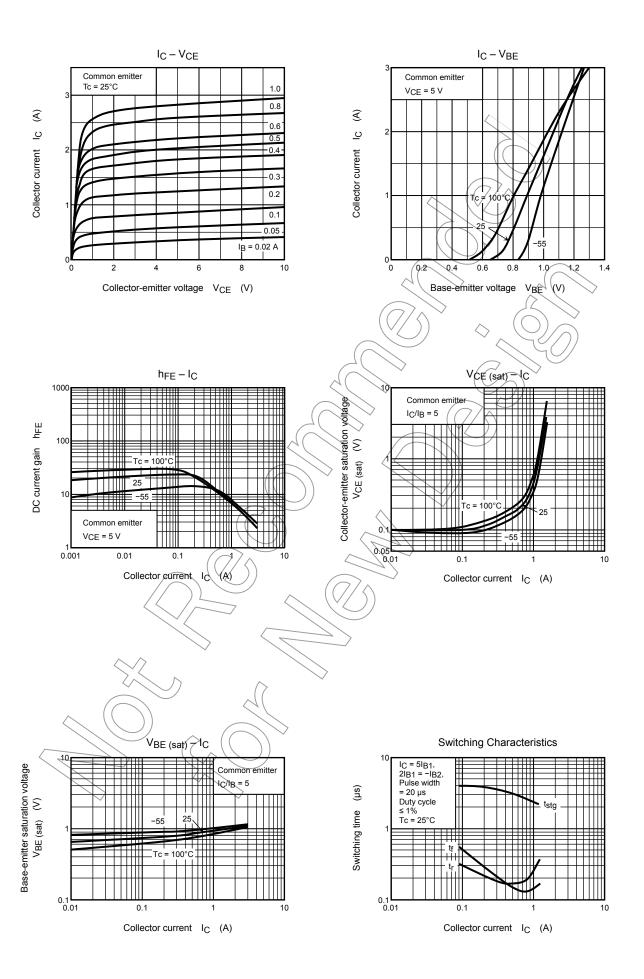
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

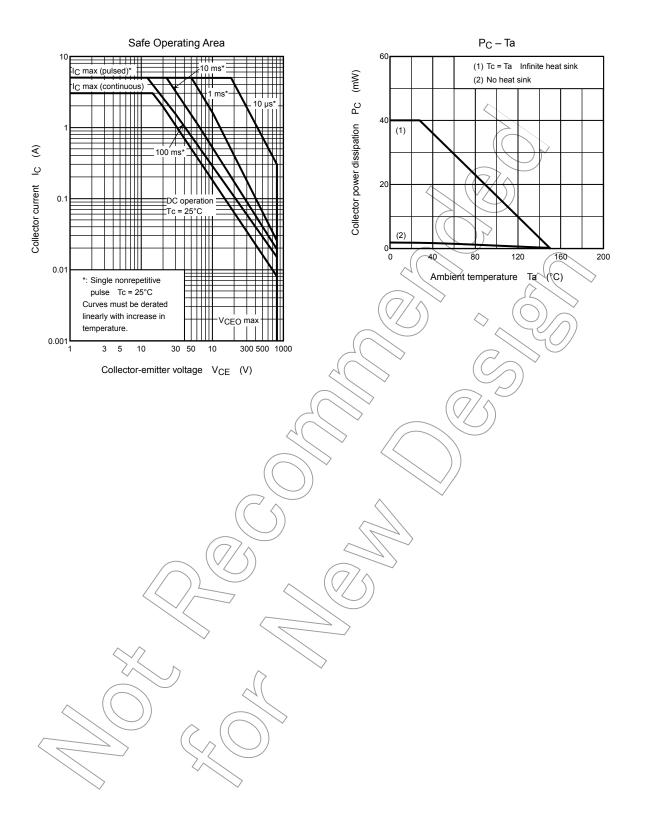
Electrical Characteristics (Tc = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off	current	I _{CBO}	V _{CB} = 720 V, I _E = 0	_	_	100	μA
Emitter cut-off cu	rrent	I _{EBO}	V _{EB} = 7 V, I _C = 0	_	_	10	mA
Collector-base br	eakdown voltage	V (BR) CBO	I _C = 1 mA, I _E = 0	900	_	_	V
Collector-emitter	breakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	800	_	_	V
DC current gain		h _{FE (1)}	V _{CE} = 5 V, I _C = 1 mA) /-	_	
		h _{FE (2)}	V _{CE} = 5 V, I _C = 0.15 A	15	_	_	
Collector-emitter saturation voltage V _{CE}		V _{CE} (sat)	I _C = 1.2 A, I _B = 0.24 A	$\bigcirc)$	_	1.0	V
Base-emitter saturation voltage V _{BE} (sat)		V _{BE (sat)}	I _C = 1.2 A, I _B = 0.24 A	_	_	1.3	V
Switching time S	Rise time	t _r	V _{CC} ≈ 360 V C; 20 µs Input B1 Output Output	_		0.7	
	Storage time	t _{stg}				> 4.0	μs
	Fall time	t _f	I _{B1} = 0.24 A, I _{B2} = -0.48 A, duty cycle ≤ 1%		_	0.5	











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20070701-EN

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